

EUV-FEL Light Source for Lithography

Norio Nakamura

High Energy Accelerator Research Organization(KEK)

Outline

- Introduction
- Design and Performance
- Considerations and Developments for Industrialization
 - Availability
 - Size Reduction
- Summary

Outline

- Introduction
- Design and Performance
- Considerations and Developments for Industrialization
 - Availability
 - Size Reduction
- Summary

Status & Prospect of EUV Lithography

Present Status

- EUV Lithography system based on 200-W-class LPP source is progressing and at starting point of HVM.

Future Requirement

- 1-kW-class EUV light sources will be required to realize the production for less than 3-nm node.



It is important to develop a new-type light source such as an ERL(energy recovery linac)-based EUV FEL, which has a potential of providing 1-kW-class EUV power, even to multiple scanners simultaneously.

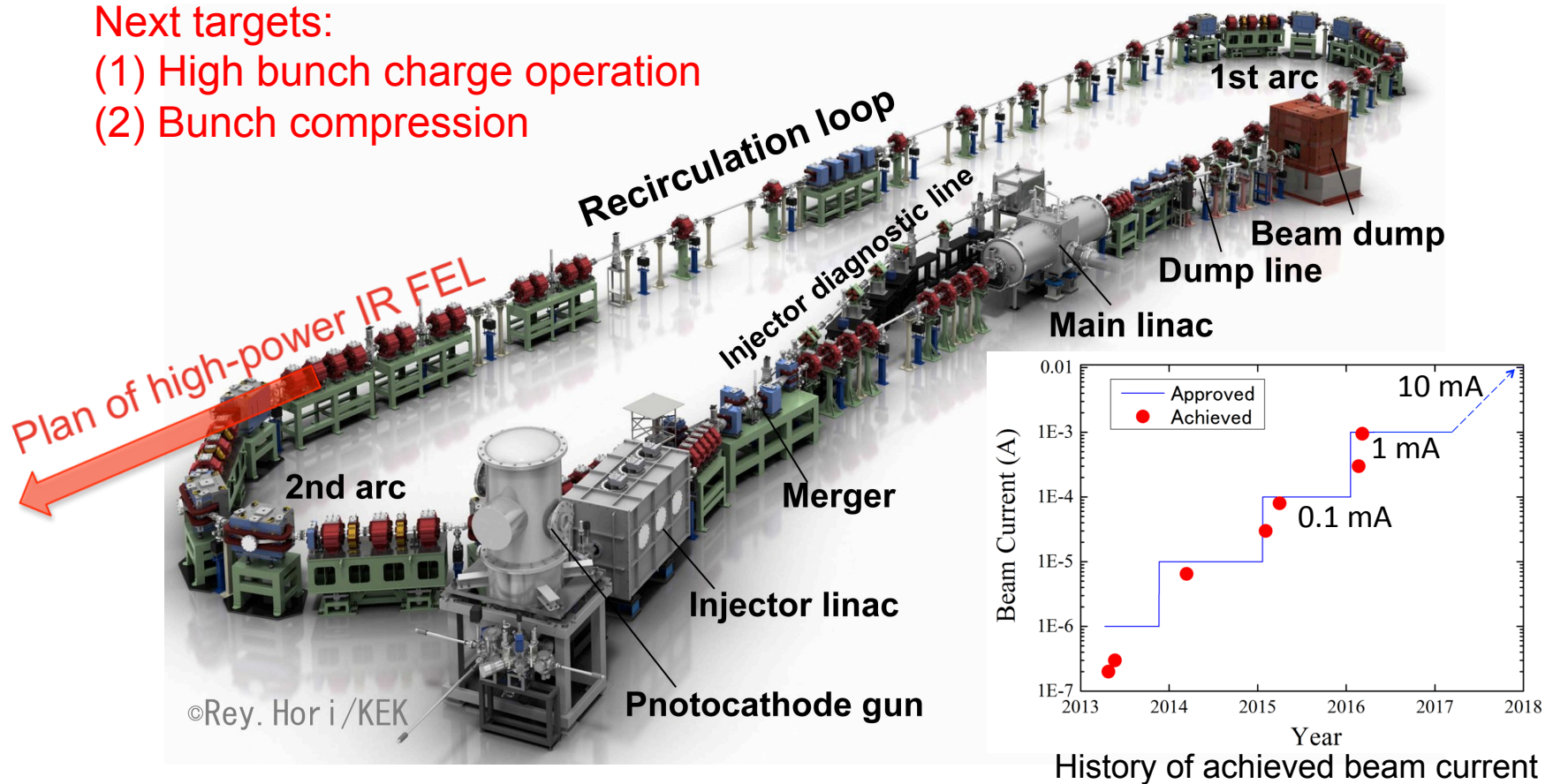
Compact ERL(cERL)

Test machine for developing ERL technologies
in operation at KEK since 2013

Beam Energy: 20 MeV
RF Frequency: 1.3 GHz
Acceleration field(ML) : 8.3 MV/m

Next targets:

- (1) High bunch charge operation
- (2) Bunch compression

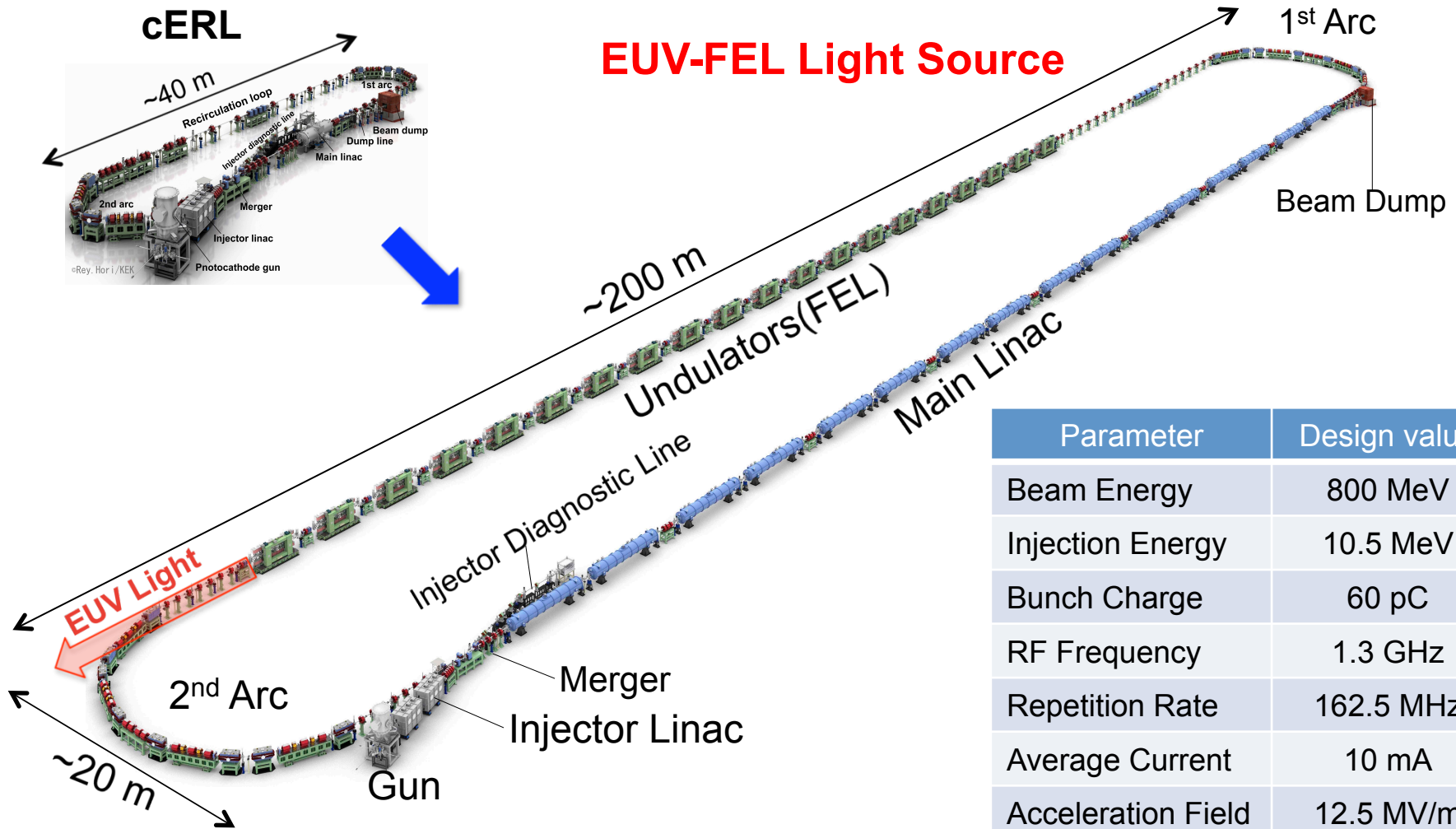


cERL technologies and resources are available for EUV-FEL light sources.

Outline

- Introduction
- **Design and Performance**
- Considerations and Developments for Industrialization
 - Availability
 - Size Reduction
- Summary

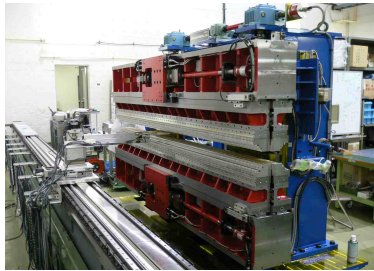
Design of EUV-FEL Light Source



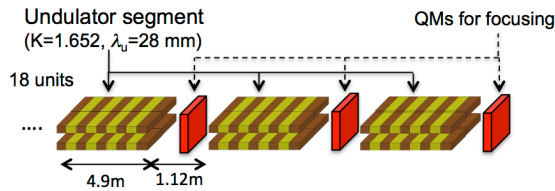
Parameter	Design value
Beam Energy	800 MeV
Injection Energy	10.5 MeV
Bunch Charge	60 pC
RF Frequency	1.3 GHz
Repetition Rate	162.5 MHz
Average Current	10 mA
Acceleration Field	12.5 MV/m
EUV Wavelength	13.5 nm
EUV Power	> 10 kW

©Rey.Hori/KEK

Light Source Components

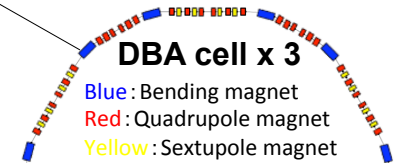


Circularly-polarizing undulator developed at KEK-PF

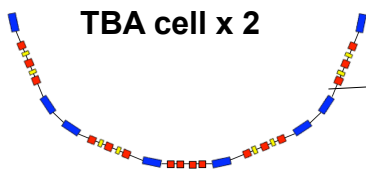


FEL system

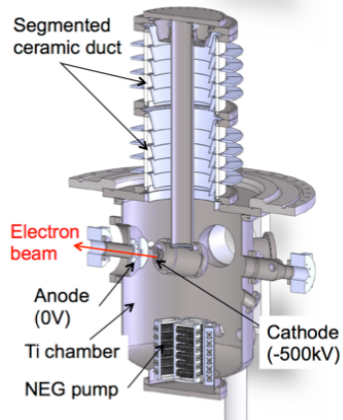
1st arc (new design) bunch compression



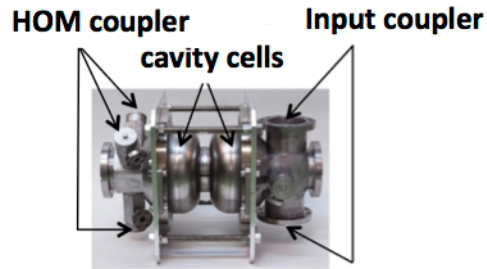
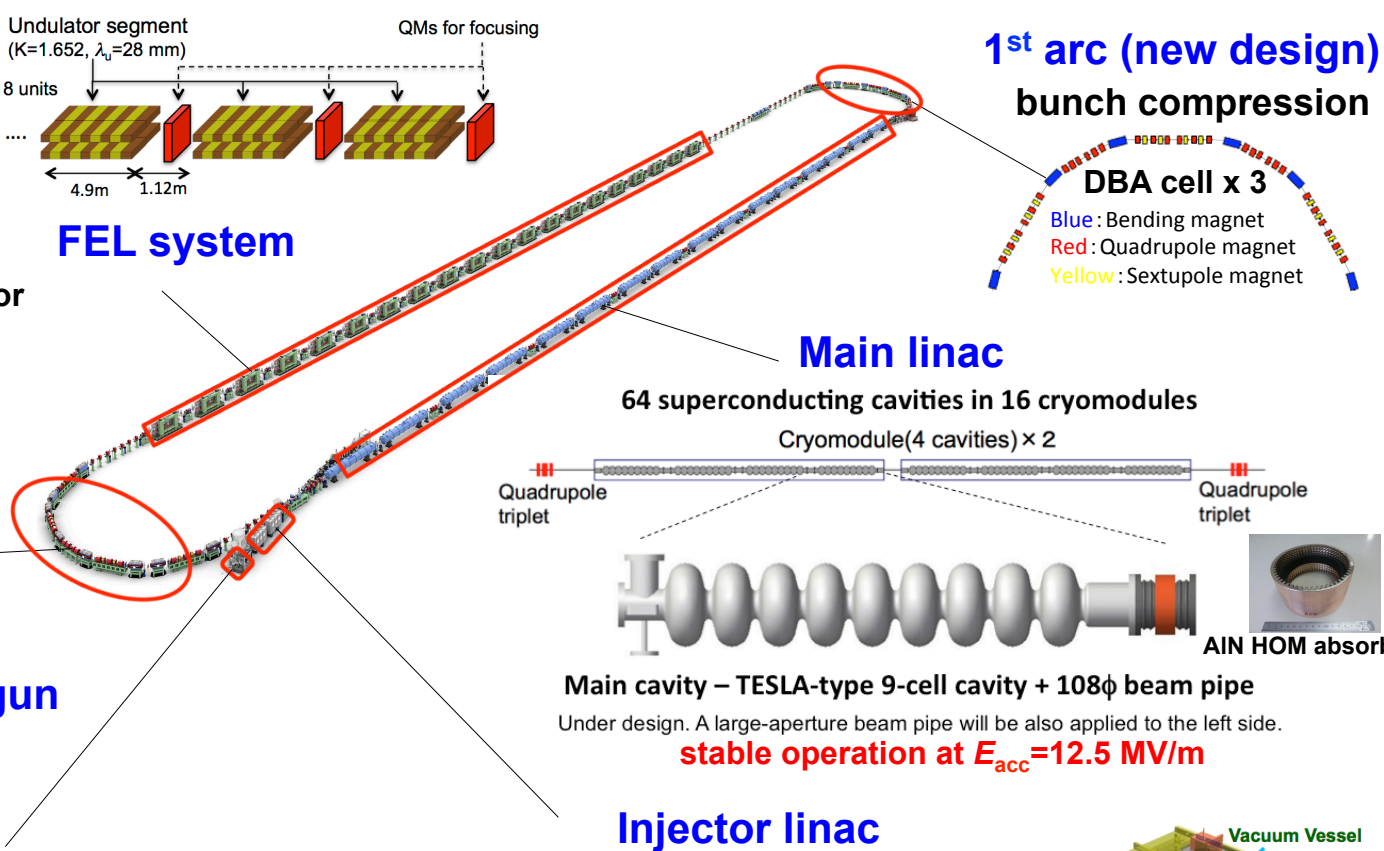
2nd arc bunch decompression



Photocathode DC gun

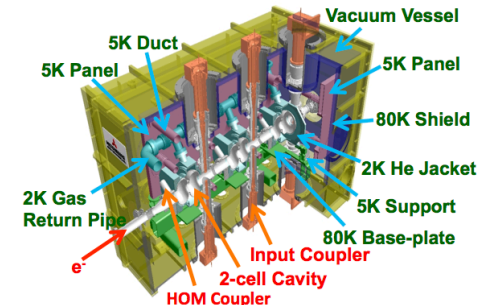


2nd DC gun developed for cERL



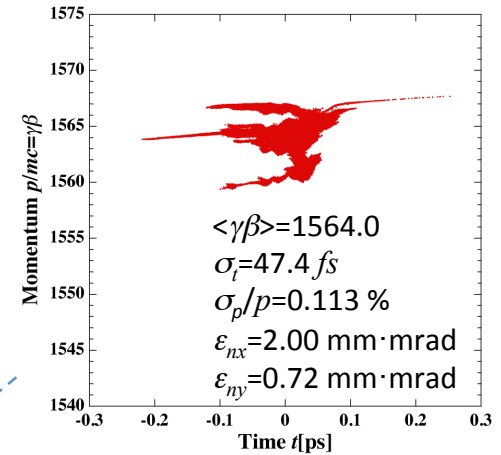
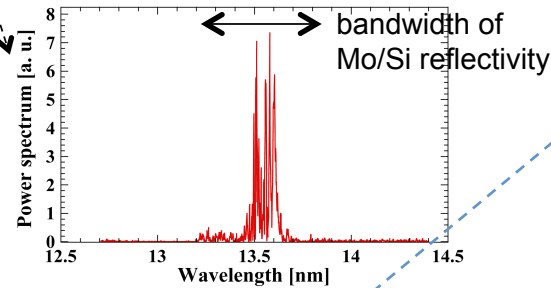
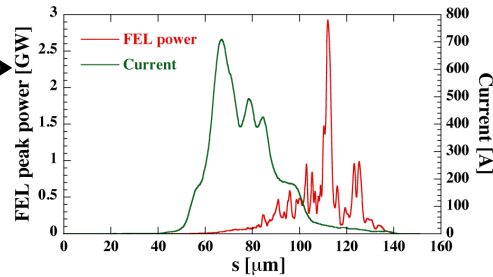
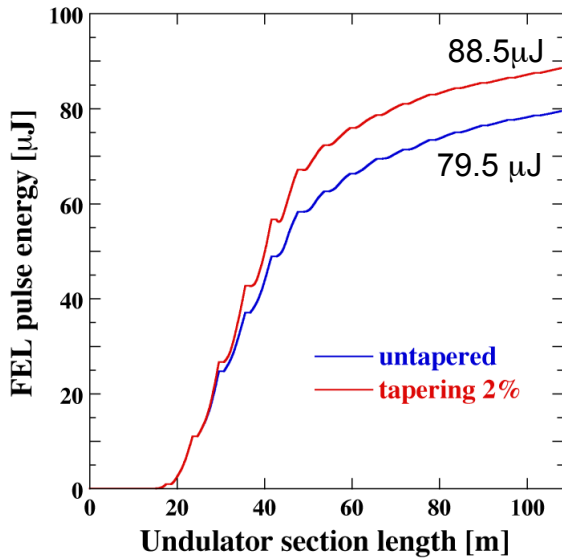
2-cell SRF cavity for cERL cERL injector cryomodule

Injector linac



cERL cryomodule structure

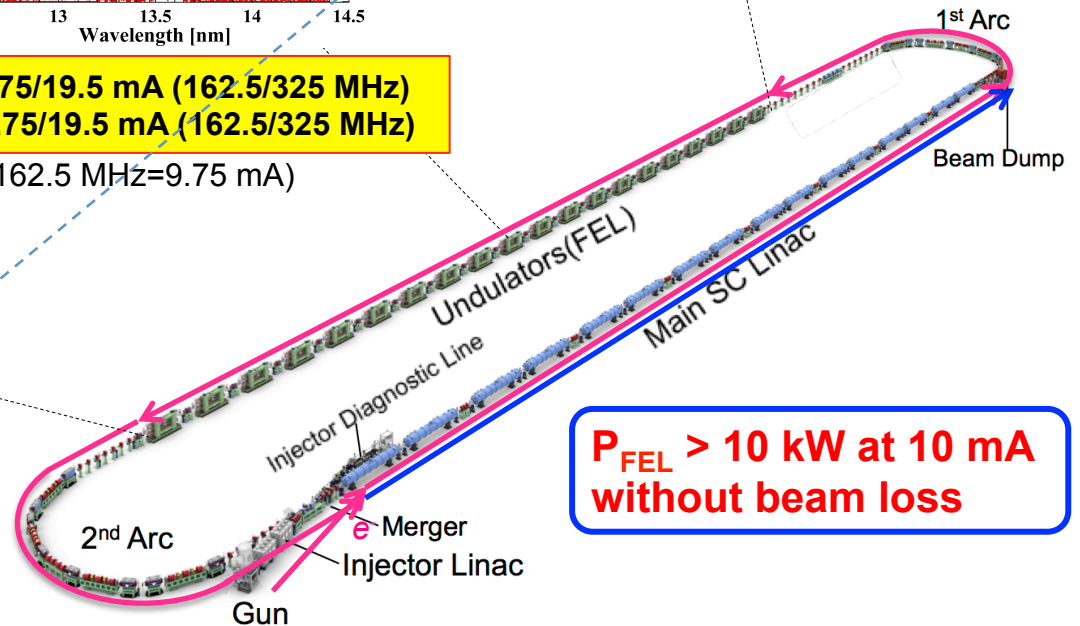
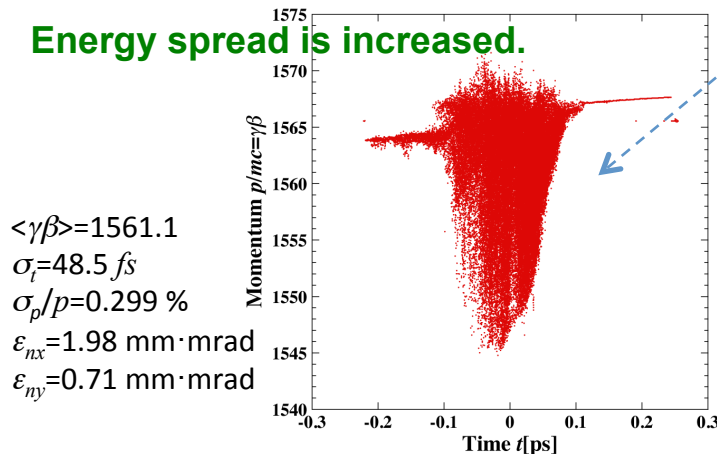
Simulation Study



FEL power without tapering: 12.9/25.8 kW @ 9.75/19.5 mA (162.5/325 MHz)
 FEL power with 2% tapering: 14.4/28.8 kW @ 9.75/19.5 mA (162.5/325 MHz)

($P_{\text{FEL}}=88.5 \mu\text{J} \times 162.5 \text{ MHz}=14.4 \text{ kW}$, $I_{\text{av}}=60\text{pC} \times 162.5 \text{ MHz}=9.75 \text{ mA}$)

Energy spread is increased.



$P_{\text{FEL}} > 10 \text{ kW}$ at 10 mA
 without beam loss

Outline

- Introduction
- Design and Performance
- Considerations and Developments for Industrialization
 - Availability
 - Size Reduction
- Summary

Availability Issues

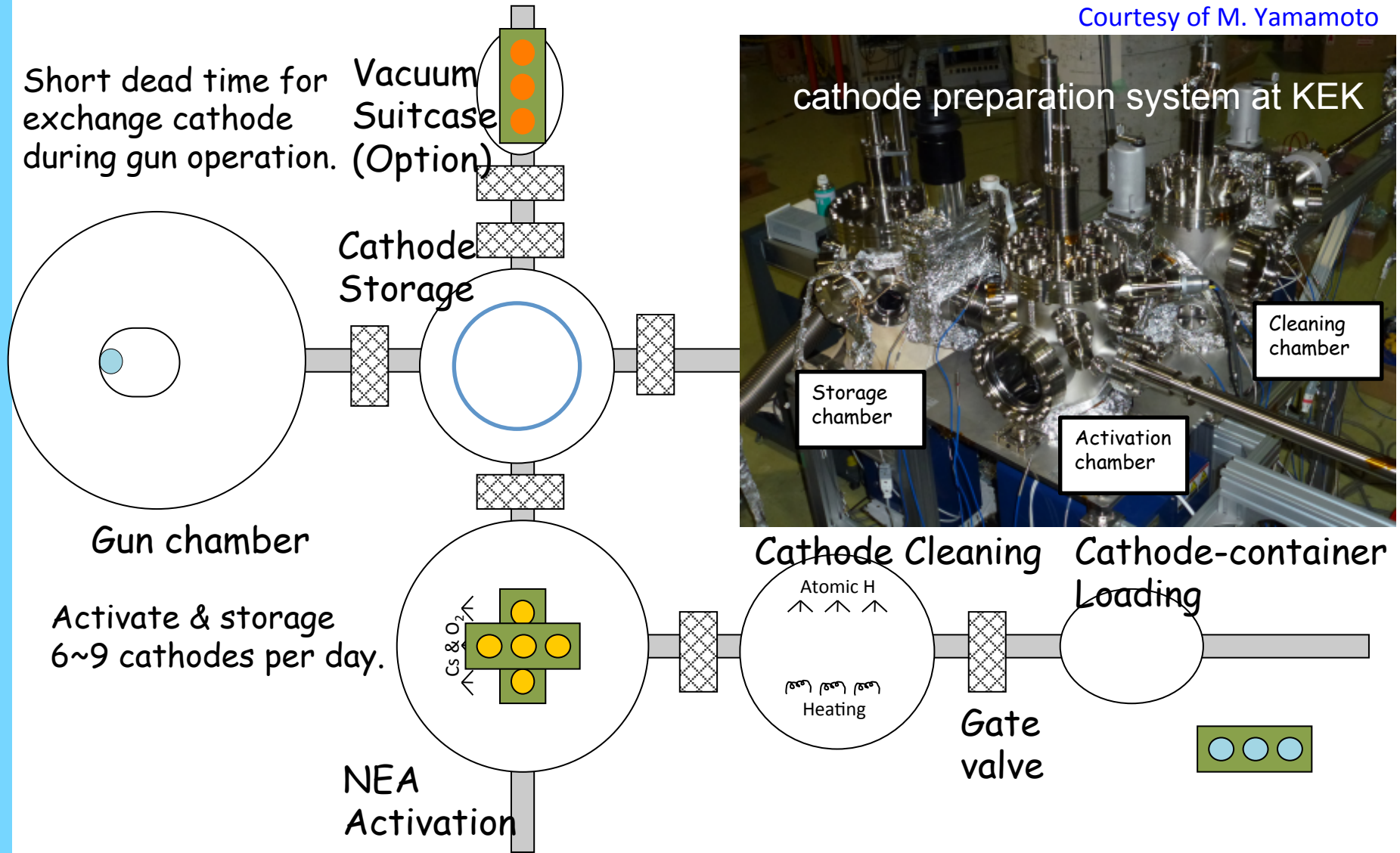
Required availability for industrialization: $\geq 98\%$
(non-operation time $\leq \sim 1$ week per year)



- Electron Gun
 - Photocathode exchange/preparation time
- SRF Cavity
 - Trip rate
 - Increase of field emission in long-term operation
- Cryoplant
 - High pressure gas safety law
 - Safety inspection (once a year in Japan)

Cathode Preparation System

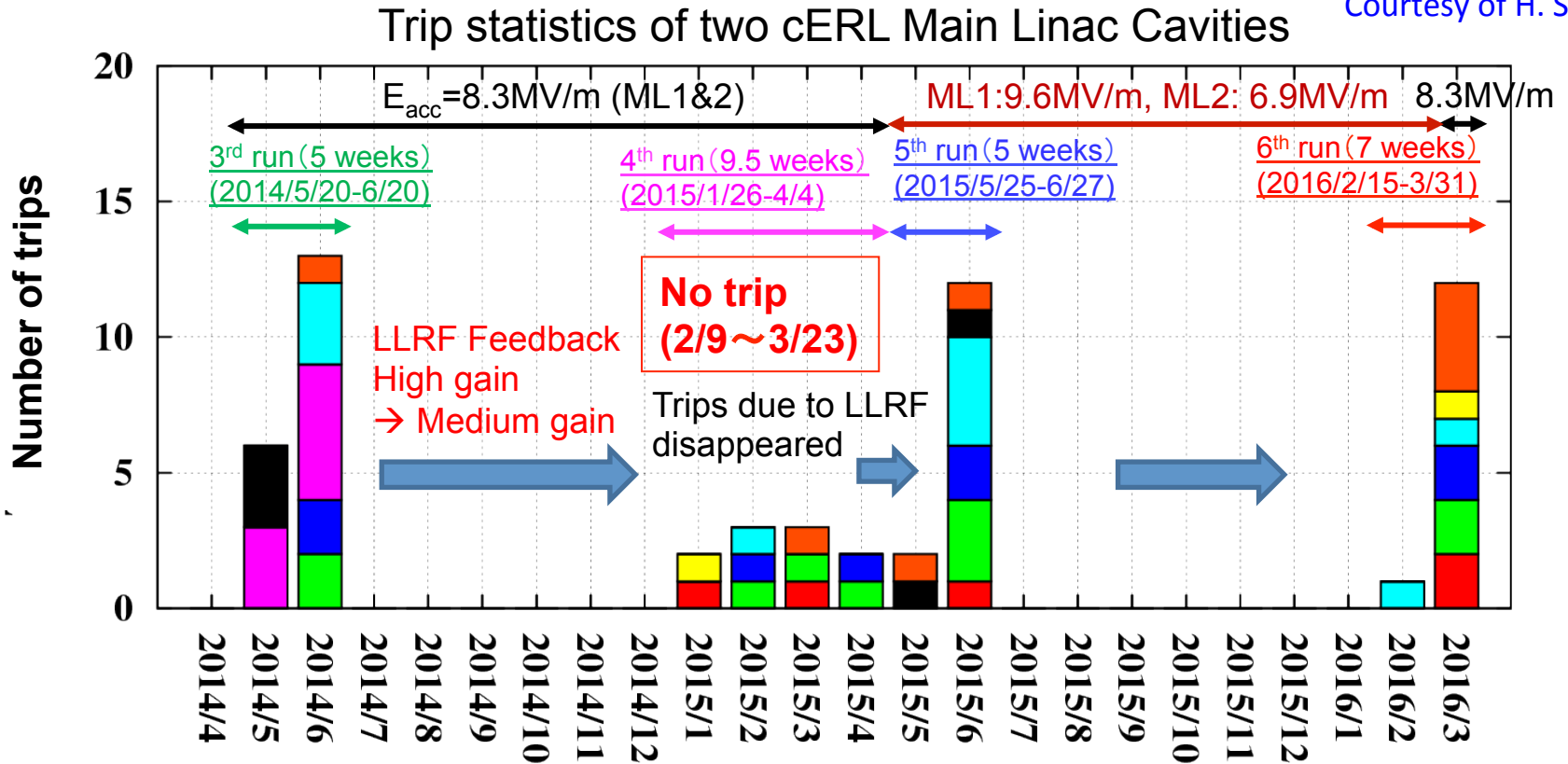
Courtesy of M. Yamamoto



Cathode preparation system should and can be remote-controlled.

Trip of SRF Cavities

Courtesy of H. Sakai



Trip rate of SRF cavities is very low and not a serious problem.

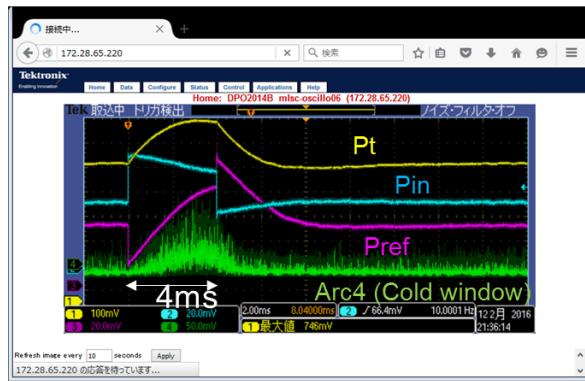


Pulse Processing of SRF Cavities

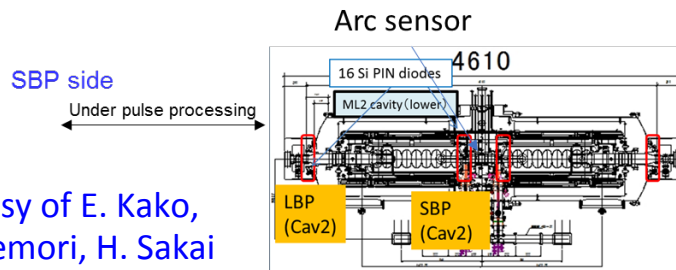
Field emission(FE) of the cERL cavities increased in the long-time operation.

High peak pulse RF power is input to the cavities to reduce FE.

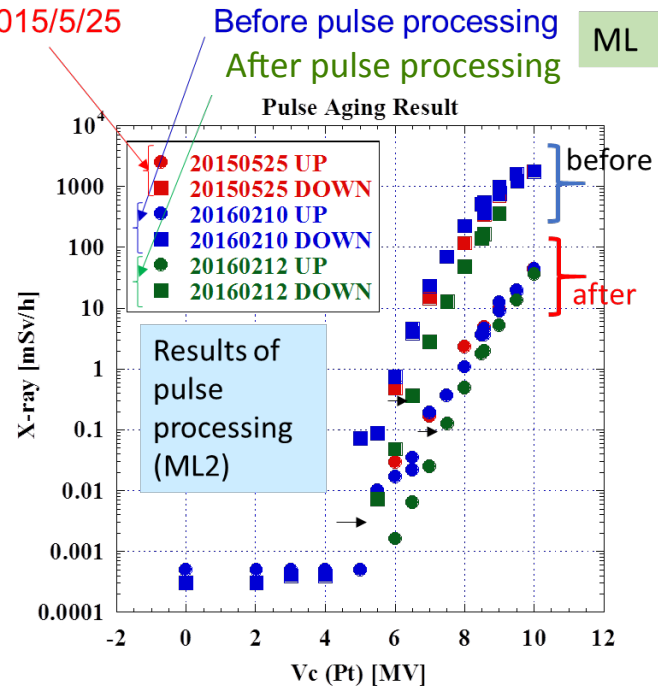
ML2 Pulse Aging (10Hz)
 $V_c = 8.57\text{MV(CW)} + 2.3\text{MV}(10\text{Hz} \times 4\text{ms}) = 10.9\text{ MV}$
 :40min pulse aging was done.



History of pulse processing: In ML, we were processing by monitoring side 32 PIN diodes



Courtesy of E. Kako, K. Umemori, H. Sakai



ML2 V_c vs ALOKA monitor

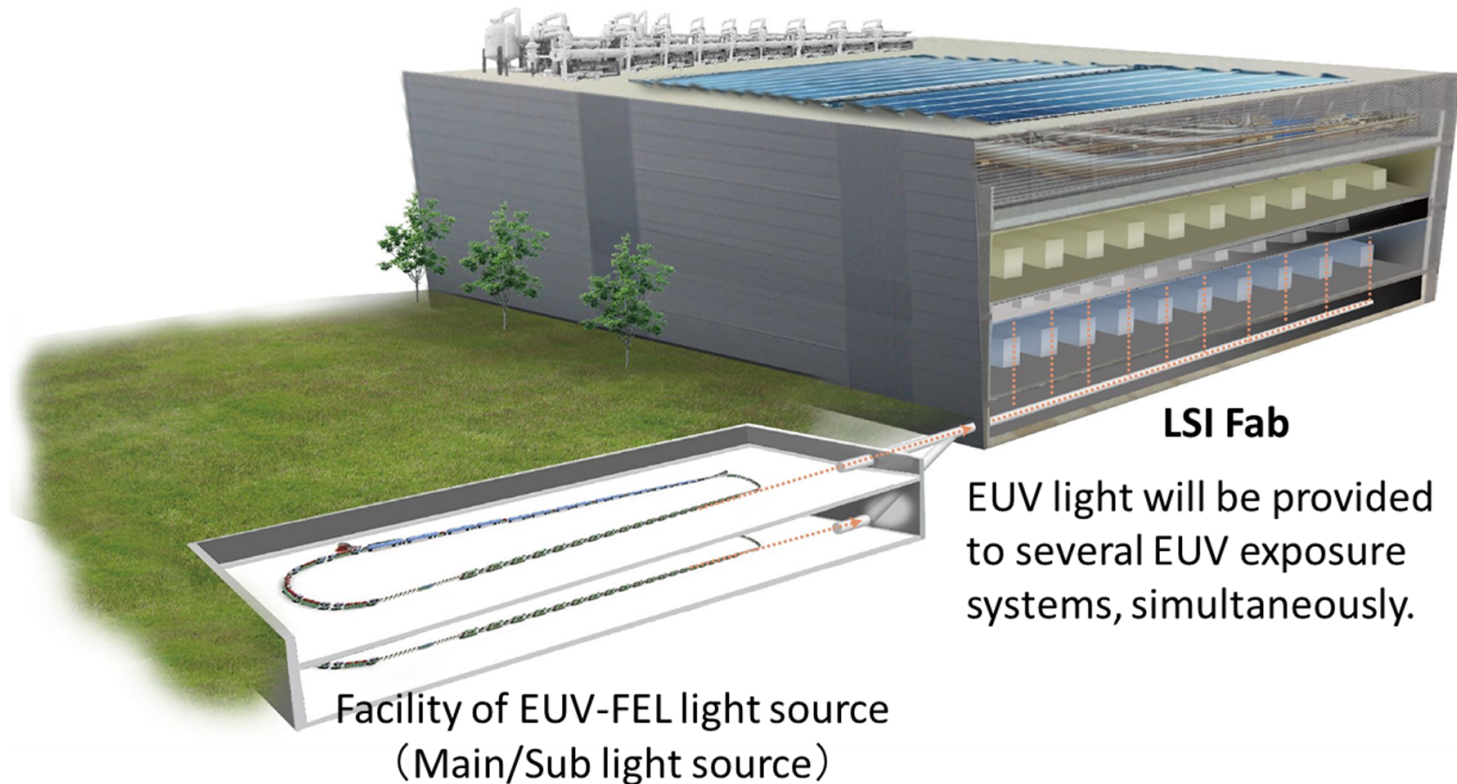
- Onset moved up 0.5 MV.
 - Radiation reduced half on same acc. field.
- Pulse processing works well.

Short-time pulse processing can recover the degraded performance.
 Other in-situ processing methods are also studied to reduce FE.

Redundant System

Redundant System for ensuring high availability

- Critical parts (Cryoplant, Injector, Main Linac, Undulator, ...)
- Entire light source system



Redundant system configuration should be designed.

Outline

- Introduction
- Design and Performance
- Considerations and Developments for Industrialization
 - Availability
 - Size Reduction
- Summary

Reduction of Light Source Size

The present size is mainly decided by the main linac length.



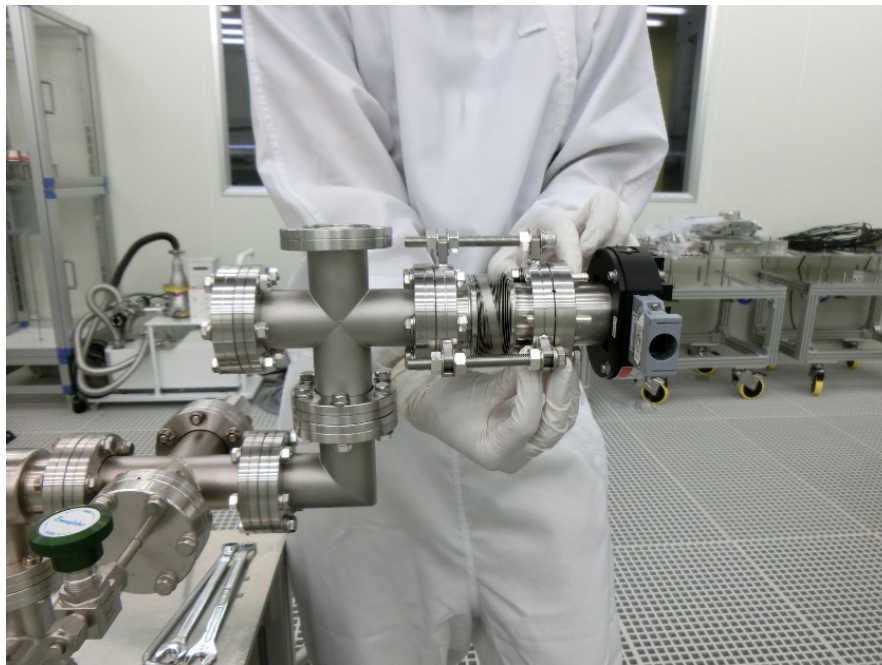
Possible solutions of reducing the main-linac length

- Higher acceleration field of main linac
 - Suppression of field emission
 - Higher-Q SRF cavity
- Lower beam energy
 - Shorter-period undulators with stronger magnetic field
 - In-vacuum undulators
 - Cryogenic permanent magnet undulators
- Double-loop configuration
 - Two-times acceleration with half the main linac
 - Division of the main linac into two parts

Suppression of Field Emission

Suppression of field emission is a key issue for higher acceleration field of main-linac SRF cavities in CW operation.

Improvement for clean environments with dust free during assembly work



Introduction of a particle measurement system in vacuum and a slow pumping and venting system for suppression of particle movement

Test bench to confirm the higher field performance of cavities



Horizontal cryostat to check cavity performance after assembly work

Courtesy of E. Kako, K. Umemori, H. Sakai

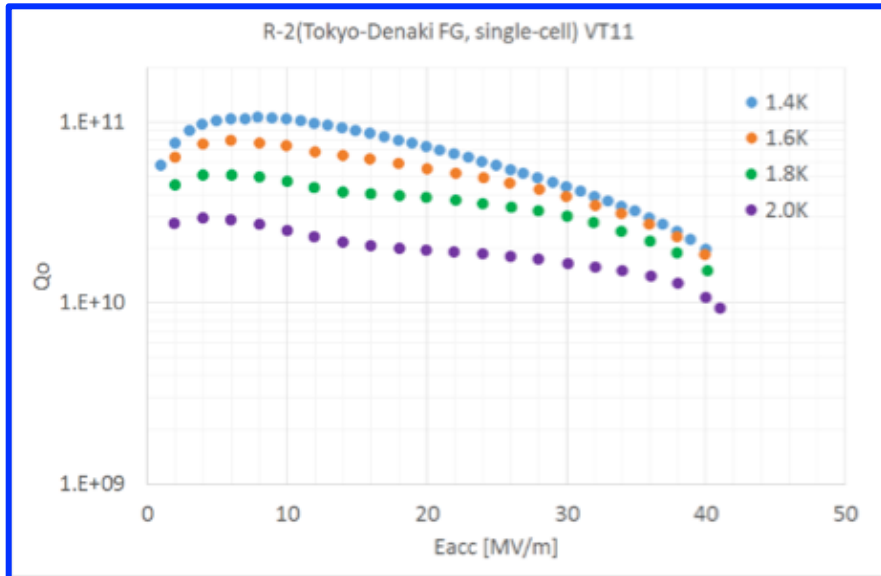
Higher-Q SRF Cavities

Power loss in SRF cavity: $P_{\text{loss}} \propto E_{\text{acc}}^2/Q$

Methods of achieving higher Q values

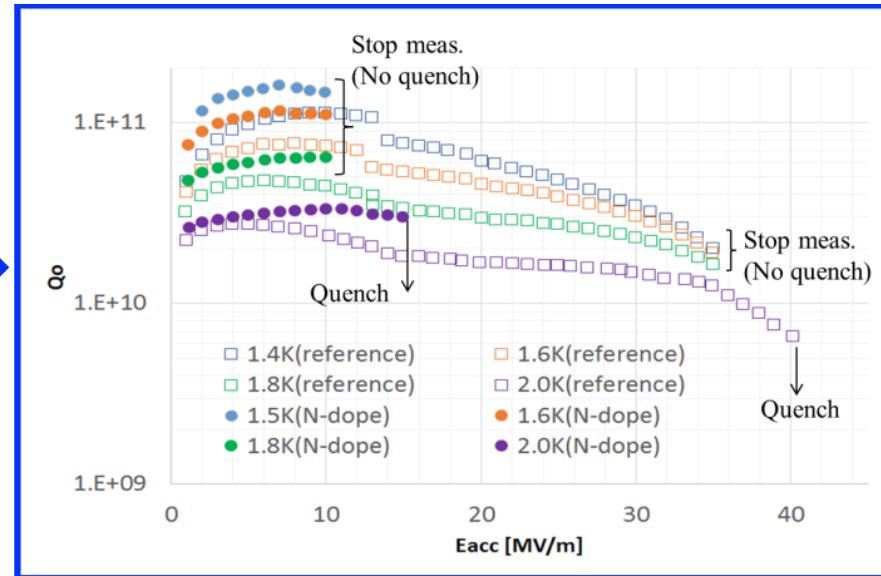
- (1) Reduction of residual magnetic field by a solenoid magnet and so on
- (2) Introduction of nitrogen(N_2) doping treatment

$Q \sim 1 \times 10^{10} \rightarrow 2 \times 10^{10}$ @ $E_{\text{acc}} = 15$ MV/m, 2K



Cancellation of the residual magnetic field by a solenoid coil

$Q = 2 \times 10^{10} \rightarrow 3 \times 10^{10}$ @ $E_{\text{acc}} = 15$ MV/m, 2K



Improvement of Q values by nitrogen doping treatment

Courtesy of E. Kako, K. Umemori, H. Sakai

Further study on N_2 doping is necessary for more optimum condition.

Shorter Period Undulators (1)

- Shorter period undulators for reducing beam energy
- (1) In-vacuum undulators (IVUs)
 - (2) Cryogenic permanent magnet undulators (CPMUs)

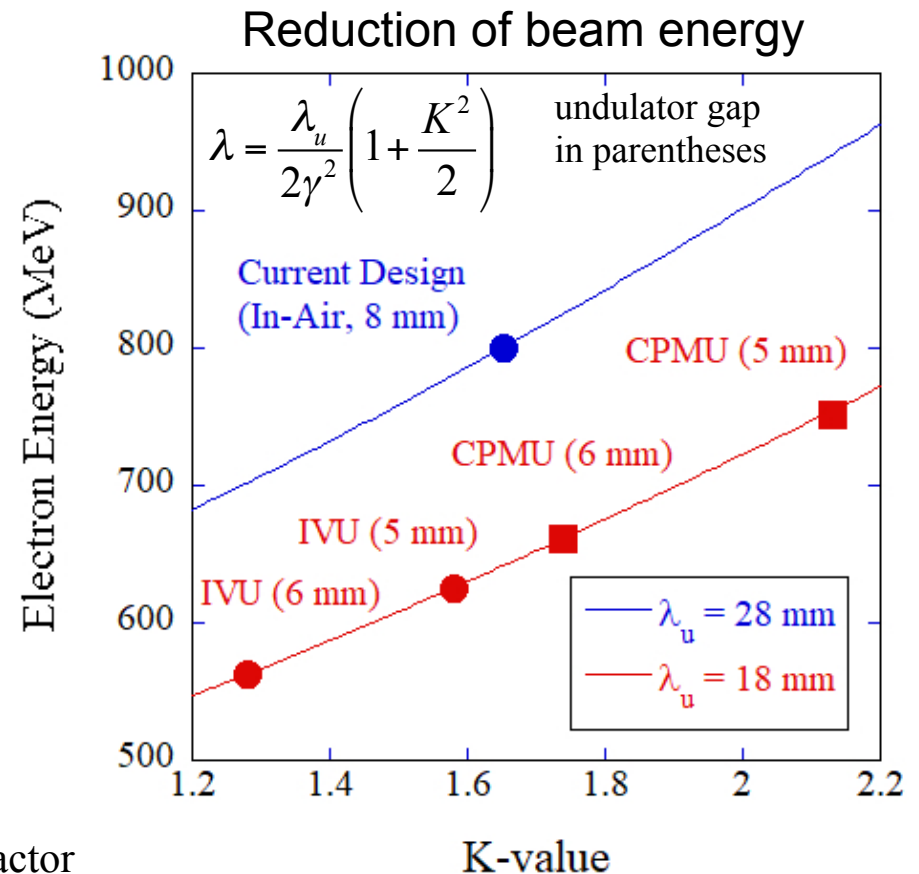
Beam parameters assumed
in the calculation

Energy spread	0.1 %
Charge	60 pC/bunch
Bunch length	100 fs
Peak current I_p	600 A
Average current	9.75 mA
Normalized emittance ($\epsilon_x = \epsilon_y$)	1 mm mrad
Beta func. ($\beta_x = \beta_y$)	5 m
Repetition frequency	162.5 MHz

λ : radiation wavelength(13.5 nm)

λ_u : undulator period

K : K-value of undulator γ : Lorentz factor



Shorter Period Undulators (2)

FEL Output Power

$$P_{FEL} = \eta P_b \quad (P_b = E_b I_b)$$

$$\eta = 1.6 \rho / (1 + \Lambda)^2$$

$$\rho^3 = \frac{1}{64\pi^2} \left(\frac{K\lambda_u}{\gamma} \right)^2 \frac{I_p [JJ]^2}{I_A r_b^2 \gamma}$$

P_{FEL} : FEL output power P_b : beam power

E_b : beam energy I_b : average beam current

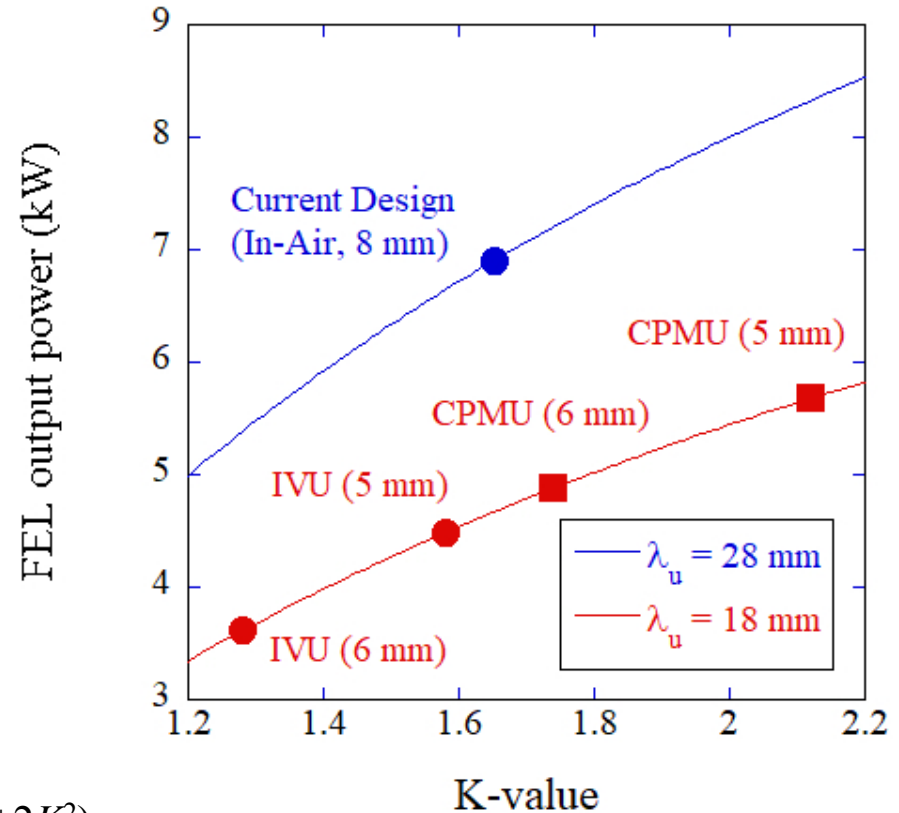
η : energy conversion efficiency

ρ : one-dimensional FEL parameter

Λ : correction term for three-dimensional effects

I_p : peak current, I_A : Alfven current

r_b : transverse beam size $JJ: J_0(\xi) - J_1(\xi)$, $\xi = K^2 / (4 + 2K^2)$



Courtesy of R. Kato

Conclusions:

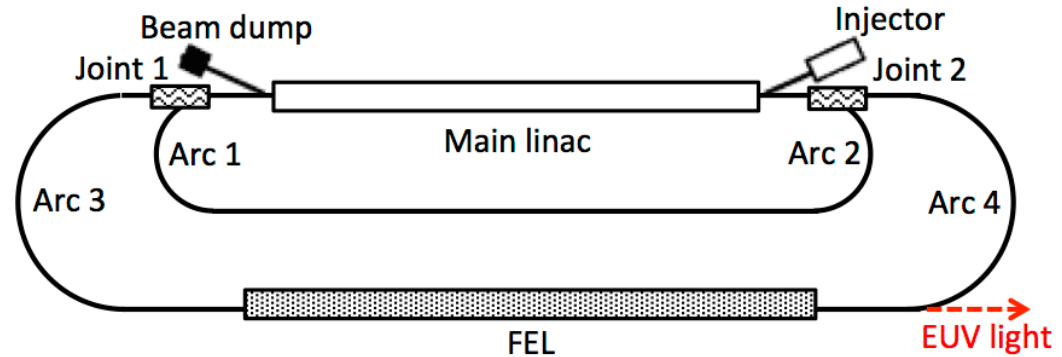
- (1) The beam energy and the main-linac length are reduced.
- (2) The FEL output power is also decreased (without current increase).

Double-Loop Configuration

Type A:

Beam is accelerated twice by the same main-inac(ML) cavities and the ML length is reduced by half.

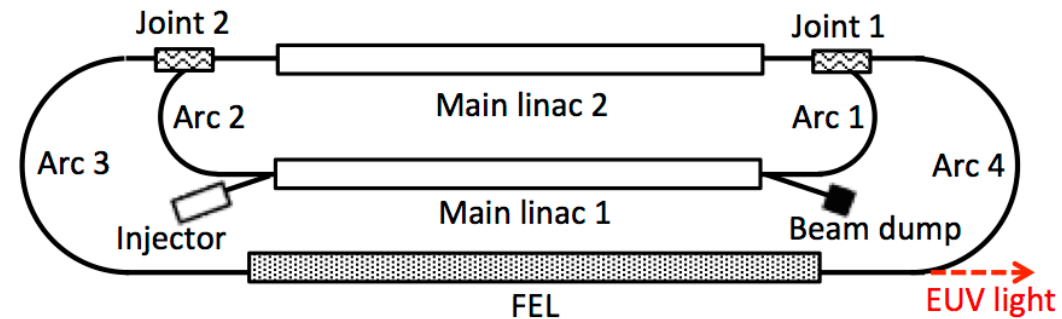
The beam current and the higher-order-mode(HOM) power in ML become double.



Type B:

Main linac(ML) is divided into two and each ML length becomes half. The beam current and the HOM power in ML are the same.

The number of the ML cavities is doubly larger than that of Type-A configuration.



Joint 1 & 2 consist mainly of bending magnets.

- Light source size is significantly reduced.
- Design study is needed to keep the same EUV output power.

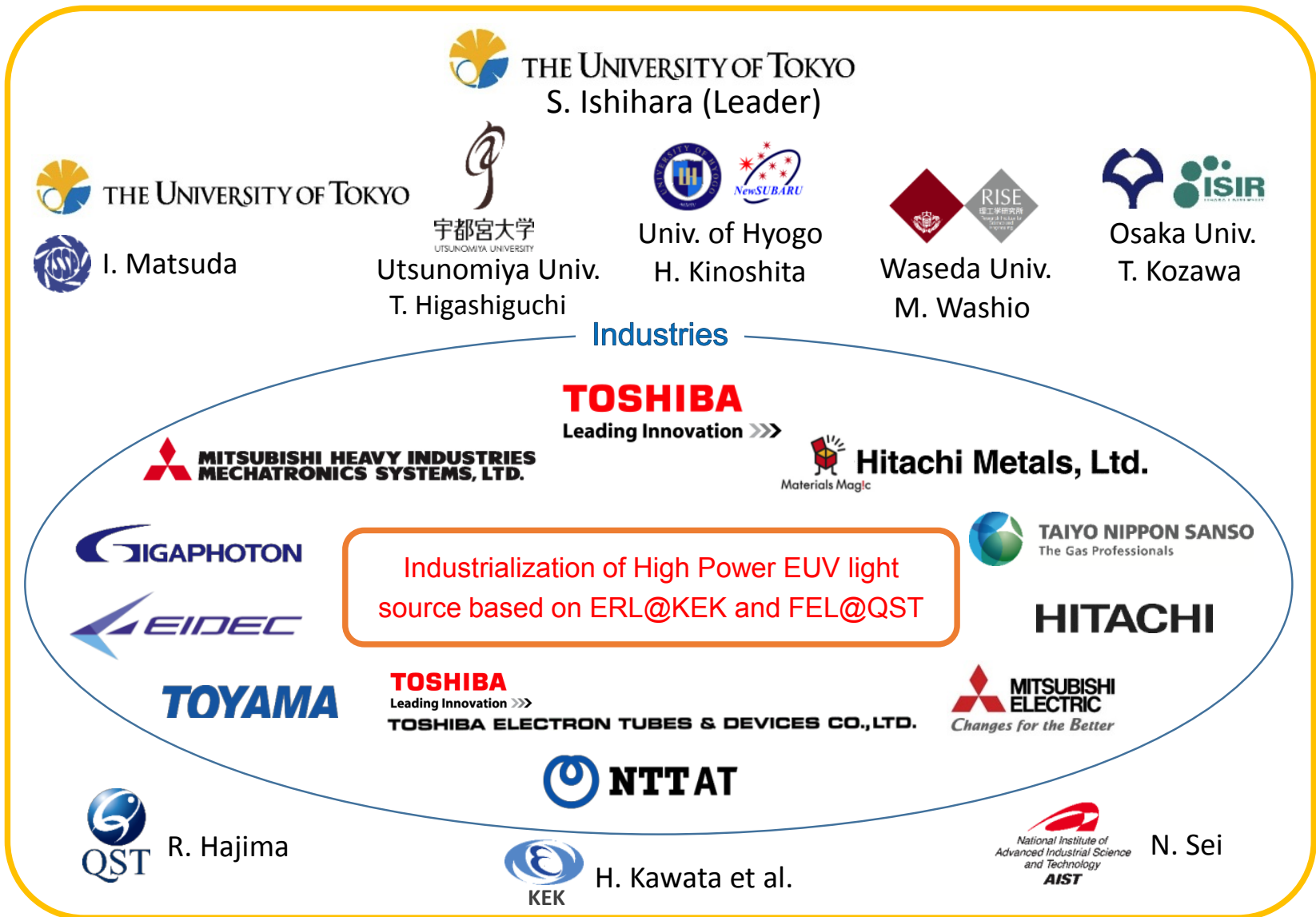
Outline

- Introduction
- Design and Performance
- Considerations and Developments for Industrialization
 - Availability
 - Size Reduction
- **Summary**

Summary

- ERL-based EUV-FEL light sources have a potential of providing high-power EUV light that meets future demand for lithography.
- It is demonstrated in simulation that our designed EUV-FEL light source can generate EUV power of more than 10 kW at 10 mA without serious beam loss.
- High availability required for lithography can be achieved without too much technology development and with a redundant system.
- Reduction of the light source size is also possible and requires further R&D and design work.

EUV-FEL Light Source Study Group for Industrialization



EUV-FEL Design Group



(KEK) T. Furuya, K. Haga, I. Hanyu, K. Harada, T. Honda, Y. Honda, E. Kako, Y. Kamiya, R. Kato, H. Kawata, Y. Kobayashi, T. Konomi, T. Kubo, S. Michizono, T. Miura, T. Miyajima, H. Nakai, N. Nakamura, T. Obina, K. Oide, H. Sakai, M. Shimada, R. Takai, Y. Tanimoto, K. Tsuchiya, K. Umemori, S. Yamaguchi, M. Yamamoto



(QST) R. Hajima



東北大学

(Tohoku Univ.) N. Nishimori

The design study has been done under collaboration with a Japanese company.

Thank you for your attention!

